National Semiconductor

Preliminary

June 1979

INS8048-Series Microcomputer/Microprocessor Family

General Description

The INS8048/49/50-Series microcomputers and the INS8035/39/40-Series microprocessors (hereinafter referred to as the 48-Series) are self contained, 8-bit parallel, 40-pin. dual in-line devices fabricated using National Semiconductor's scaled N-channel, silicon gate MOS process, XMOS. The 48-Series devices contain the system timing, control logic, ROM (where applicable) program memory, RAM data memory and 27 I/O lines necessary to implement dedicated control functions. All 48-Series devices are pin compatible, differing only in the size of on-board ROM (where applicable) and RAM as shown below:

DEVICE	RAM ARRAY	ROM ARRAY
INS8048	64 x 8	1K x 8
INS8049	128 x 8	2K x 8
INS8050	256 x 8	4K x 8
INS8035	64 x 8	N/A
INS8039	128 x 8	N/A
INS8040	256 x 8	N/A

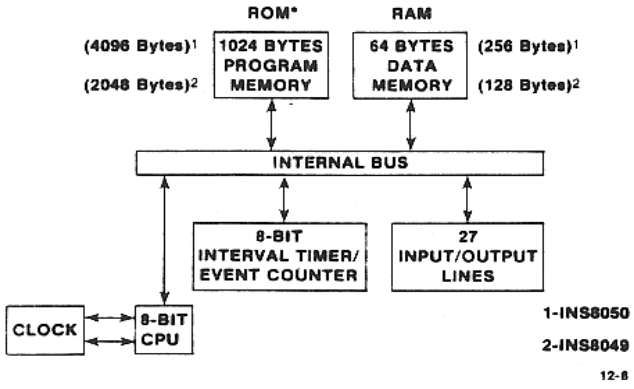
The devices are designed to be efficient controllers. They have extensive bit handling capability as well as facilities for both binary and BCD arithmetic. Efficient use of program memory is derived from an instruction set comprised predominantly of single bytes. The remaining instructions are two bytes in length. Additional external memory may be added up to a maximum of 4K bytes of program memory and 256 bytes of data memory without paging.

Features

- 8-Bit CPU, RAM, ROM, I/O in Single Package
- 2.5 µsec Cycle, 6 MHz Clock; 1.36 µsec Cycle, 11 MHz Clock
- On-Chip Crystal Oscillator and Clock (or External Source)
- 27 I/O Lines
- Expandable Memory and I/O
- 8-Bit Timer/Counter
- Single Level Interrupt
- Interrupt has Schmitt Trigger with Hysteresis%r*%r
- Over 90 Instructions (Most Single Byte)
- Binary and BCD Arithmetic
- Single +5V Power Supply
- Low Standby Power Mode%r*%r
- Memory on Standby is Programmable%r*%r
- Low Voltage Standby (2.2V Min)%r*%r
- On-Chip Battery Charging%r*%r
- Counter Increment, Non-Increment Option

NOTE: *Transparent improvements over industry standard part.*

48-Series Block Diagram



*Not Applicable to INS8035/39/40

Absolute Maximum Ratings

Temperature Under Bias..... 0° C to +70° C
Storage Temperature..... -65° C to +150° C
All Input or Output Voltages with respect Vss.....-0.5V to +7.0V
Power Dissipation.....1.5 Watt

NOTE: *Absolute maximum ratings indicate limits beyond which permanent damage may occur. Continuous operation at these limits is not intended; operation should be limited to those conditions specified under DC Electrical Characteristics.*

DC Electrical Characteristics

T_A = 0° C to +70° C, $V_{cc} = V_{dd}$ = +5V ±10%, V_{cc} = OV. unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
V_{IL}	Input Low Voltage (All except XTAL1, XTAL2)	-0.5	0.8	0.8	V	
V_{IH}	Input High Voltage (All except XTAL1, XTAL2)	2.0		V_{CC}	V	
V_{IH1}	Input High Voltage (XTAL1, XTAL2)	3.0		V_{CC}	V	
V_{OL}	Output Low Voltage			0.4	V	I_{OL}=2.0mA
V_{OH}	Output High Voltage All except ports	3.0			V	I_{OH}= 100 µA
V_{OH1}	Port Option 2, Programmable Transistor Drive	1.5			V	I_{OH}= 1.5mA(1)
V_{OH2}	Port Option 1, Port TTL (Std. Drain)	2.4			V	I_{OH}≥ 125 µA (1)
V_{OH3}	Port Option 3 (Open Drain)			-10.0	µA	$V_{CC} \geq V_{out} \geq 0.40$
$I_{DD (32)}$	32 words on Standby Current (2)			3.0	mA	at 2.2V supply
$I_{DD (64)}$	64 words on Standby Current (2)			5.0	mA	
$I_{DD (96)}$	96 words on Standby Current (2)			7.0	mA	8049, 8050 only
$I_{DD (128)}$	128 words on Standby Current (2)			9.0	mA	8049, 8050 only
$I_{DD (160)}$	160 words on Standby Current (2)			11.0	mA	8050 only
$I_{DD (192)}$	192 words on Standby Current (2)			13.0	mA	8050 only
$I_{DD (224)}$	224 words on Standby Current (2)			15.0	mA	8050 only
$I_{DD (256)}$	256 words on Standby Current (2)			17.0	mA	8050 only
$I_{DD}+I_{CC}$	Total Supply Current 8048		75	100	mA	T_A= 25° C
$I_{DD}+I_{CC}$	Total Supply Current 8049			110	mA	T_A= 25° C
$I_{DD}+I_{CC}$	Total Supply Current 8050			120	mA	T_A= 25° C
I_{DDC}	Battery Charging Current				mA	*See Figure 5*

Notes: **1.** Port pullup current is mask programmable.

2. Location and number of words of RAM on stand-by are programmable. Current with 2.2V (2 Nickel Cadmium cells).

AC Electrical Characteristics - INS80XX-6 (1-6 MHz part)

T_A = 0° C to + 70° C, V_{cc} = +5V ±10%, V_{ss} = 0V, 2.2V < V_{oo} < 5.5 V, unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
t_{LL}	ALE Pulse Width	400			Ns	Note 1
t_{AL}	Address Setup to ALE	150			Ns	Note 1
t_{LA}	Address Hold from ALE	80			Ns	Note 1
t_{CC}	Control Pulse Width					
	$\overline{PSEN}$, $\overline{RD}$, $\overline{WR}$	700			Ns	Note 1
t_{DW}	Data Set-Up Before $\overline{WR}$	500			Ns	Note 1
t_{WD}	Data Hold After $\overline{WR}$	120			Ns	CL = 20 pF
t_{CY}	Cycle Time	2.5		15.0	Ns	1 to 6 MHz XTAL
t_{DR}	Data Hold	0		200	Ns	
t_{RD}	PSEN, RD to Data In			500	Ns	
t_{AW}	Address Setup to WR	230			Ns	
t_{AD}	Address Setup to Data In			950	Ns	
t_{AFC}	Address Float to RD, PSEN	0			Ns	

Port 2 Timing

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
t_{CP}	Port Control Setup before Falling Edge of PROG	110			Ns	Note 1
t_{PC}	Port Control Hold after Falling Edge of PROG	140			Ns	Note 1
t_{PR}	PROG to Time P2 Input must be Valid			810	Ns	Note 1
t_{DP}	Output Data Setup Time	220			Ns	Note 1
t_{PD}	Output Data Hold Time	65			Ns	Note 1
t_{PF}	Input Data Hold Time	0		150	Ns	Note 1
t_{PP}	PROG Pulse Width	1510			Ns	Note 1
t_{PL}	Port 2 I/O Data Setup	400			Ns	Note 1
t_{LP}	Port 2 I/O Data Hold	150			Ns	Note 1

AC Electrical Characteristics - INS80XX-11 (11 MHz Part)

T_A = 0° C to + 70° C, +5V ±10%, V_{ss} = 0V, 2.2V < V_{DD} < 5.5V, unless otherwise specified.

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
t_{LL}	ALE Pulse Width	150			Ns	Note 1
t_{AL}	Address Setup to ALE	70			Ns	Note 1
t_{LA}	Address Hold from ALE	50			Ns	11 MHz
t_{CC}	Control Pulse Width PSEN, RD, WR	300			Ns	Note 1
t_{DW}	Data Set-Up Before WR	250			Ns	C_L = 20 pF
t_{WD}	Data Hold After WR	40			Ns	Note 1
t_{CY}	Cycle Time	1.36		15	M	4 to 11 MHz XTAL
t_{DR}	Data Hold	0		100	Ns	Note 1
t_{RD}	PSEN, RD to Data In			200	Ns	Note 1
t_{AW}	Address Set-Up to WR	200			Ns	Note 1
t_{AD}	Address Set-up to Data In			400	Ns	Note 1
t_{AFG}	Address Float to RD, PSEN	-10			Ns	Note 1

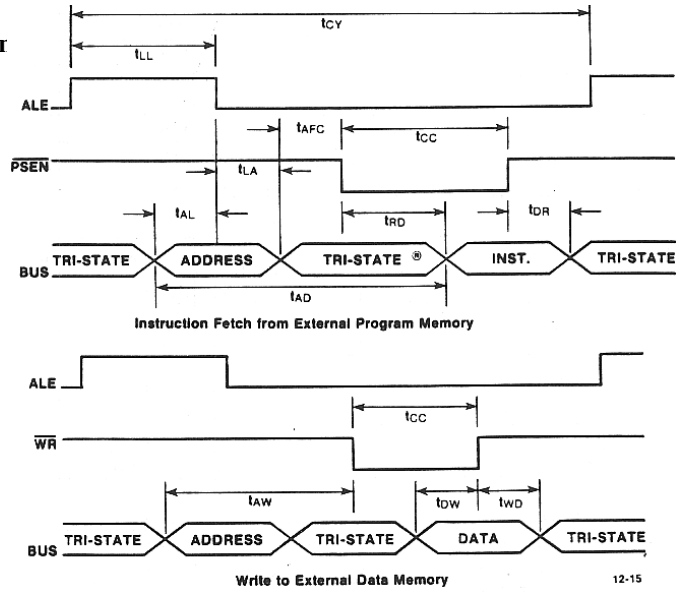
Port 2 Timing						
		%w6d				
Symbol	**Parameter**	**Min**	**Typ**	**Max**	**Units**	**Test Conditions**
		%w6d				
T_{CP}	Port Control Setup before Falling Edge of PROG	100			ns	Note 1
t_{PC}	Port Control Hold after Falling Edge of PROG	60			ns	Note 1
t_{PR}	PROG to Time P2 Input must be Valid			650	ns	Note 1
T_{DP}	Output Data Setup Time	200			ns	Note 1
t_{PD}	Output Data Hold Time	20			ns	Note 1
t_{PF}	Input Data Hold Time	0	150		ns	Note 1
t_{PP}	PROG Pulse Width	700			ns	Note 1
t_{PL}	Port 2 I/O Data Hold	20			ns	Note 1

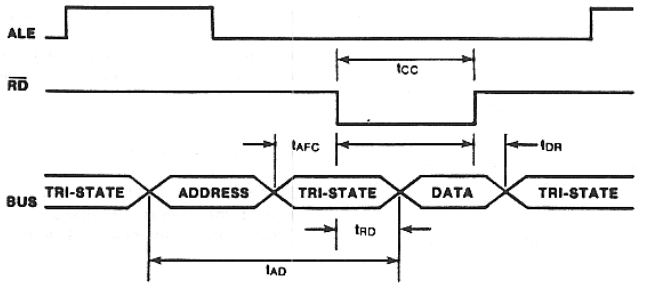
Note 1. Control outputs C_L = 80 pF; Bus outputs C_L = 150 pF.

Capacitance T_A = 25°C. V_{CC} = V_{SS} = 0V

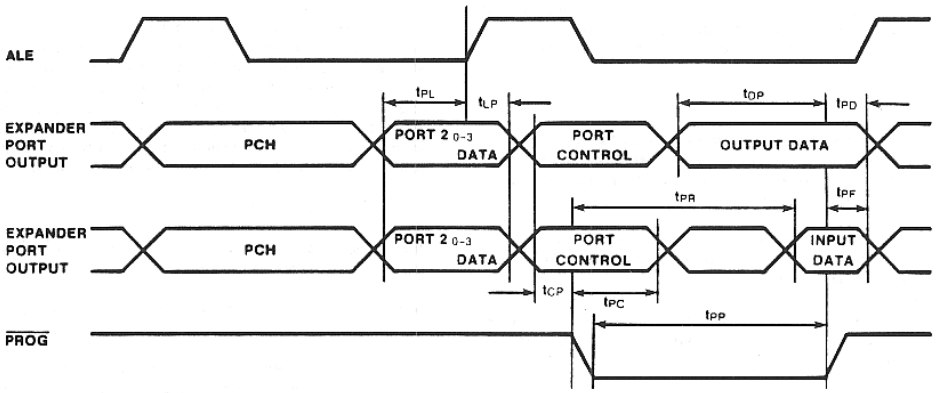
Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
C_{IN}	Input Capacitance		6	10	pF	f_c = 1 MHz
C_{OUT}	OUTPUT AND RESET Capacitance		10	20	pF	Unmeasured pins returned to V_{SS}

Timing Waveforr

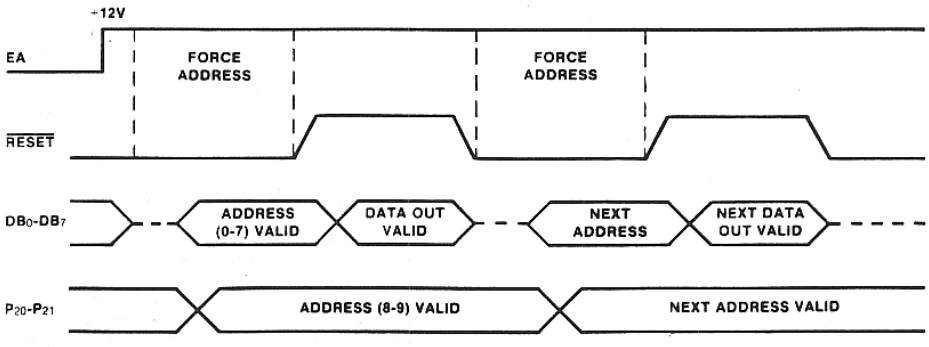




Read from External Data Memory



Port 2 Timing 12-12



Verify Mode Timing 12-13

Functional Pin Description

INPUT SIGNALS

Reset (RESET): An active low(0) input that initializes the processor and is used to verify program memory. (See note #1.)

Single Step (SS): Active low (0) input which, in conjunction with ALE, can single step the processor through each instruction.

External Access (EA): An active high (1) input that forces all program memory fetches to reference external program memory.

Testable Input 0 (T_0): Testable input pin using conditional branch functions JTO ($T_0 = 1$) or JNTO ($T_0 = 0$). T_0 can be designated as the clock output using instruction ENTO CLK.

Testable Input 1 (T_1): Testable input pin using conditional branch functions JT1 ($T_1 = 1$) or JNT1 ($T_1 = 0$). T_1 can be designated as the Timer/Counter input from an external source using instruction EN TCNTI.

Interrupt (INT): An active low input that initiates an interrupt when interrupt is enabled. Interrupt is disabled after a reset. Also can be tested with instruction JN1 (INT = 0). (See Note 2).

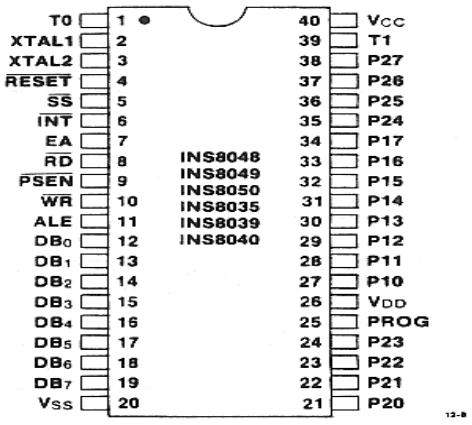
OUTPUT SIGNALS

Read Strobe (RD): An active low output strobe activated during a Bus read. Can be used to enable data onto the BUS from an external device. Used as a Read Strobe to External Data Memory.

Write Strobe (WR): An active low output strobe activated during a Bus write Used as a Write Strobe to External Data Memory.

Program Store Enable (PSEN): An active low output that occurs only during an external program memory fetch.

Pin Configuration



Address Latch Enable (ALE): An active high output that occurs once during each cycle and is useful as a clock output. The negative going edge of ALE strobes the address into external data or program memory.

Program (PROG): This output (active high) provides the output strobe for INS8243 I/O Expander.

INPUT/OUTPUT SIGNALS

Crystal Input (XTAL1, XTAL2): These two pins connect the crystal for internal oscillator operation. XTAL1 is the timing input for external source.

Port 1 (P10-P27): 8-bit quasi-bidirectional port.

Port 2 (P20-P27): 8-bit quasi-bidirectional port. During an external program memory fetch, the four high order program counter bits occur at P20-P23. They also serve as a 4-bit I/O expander bus when the INS8243 I/O Expander is used. (See note 3).

BUS (D0-D7): True bidirectional port, either statically latched or synchronous. Can be written to using WR Strobe, or Read from using RD Strobe. During an external program memory fetch, the 8 lower order program counter bits are preset at this port. The addressed instruction appears on this bus when PSEN is low. During an external RAM data store instruction. This port presents address and data under control of ALE, RD, and WR.

V_{SS}: Processor Ground potential.

V_{DD}: V_{DD} functions as the Low Power Stand-by Voltage and can vary from 2.2V to 5.5V.

V_{CC} Pin 40: Primary Power Source for 48-Series Devices.

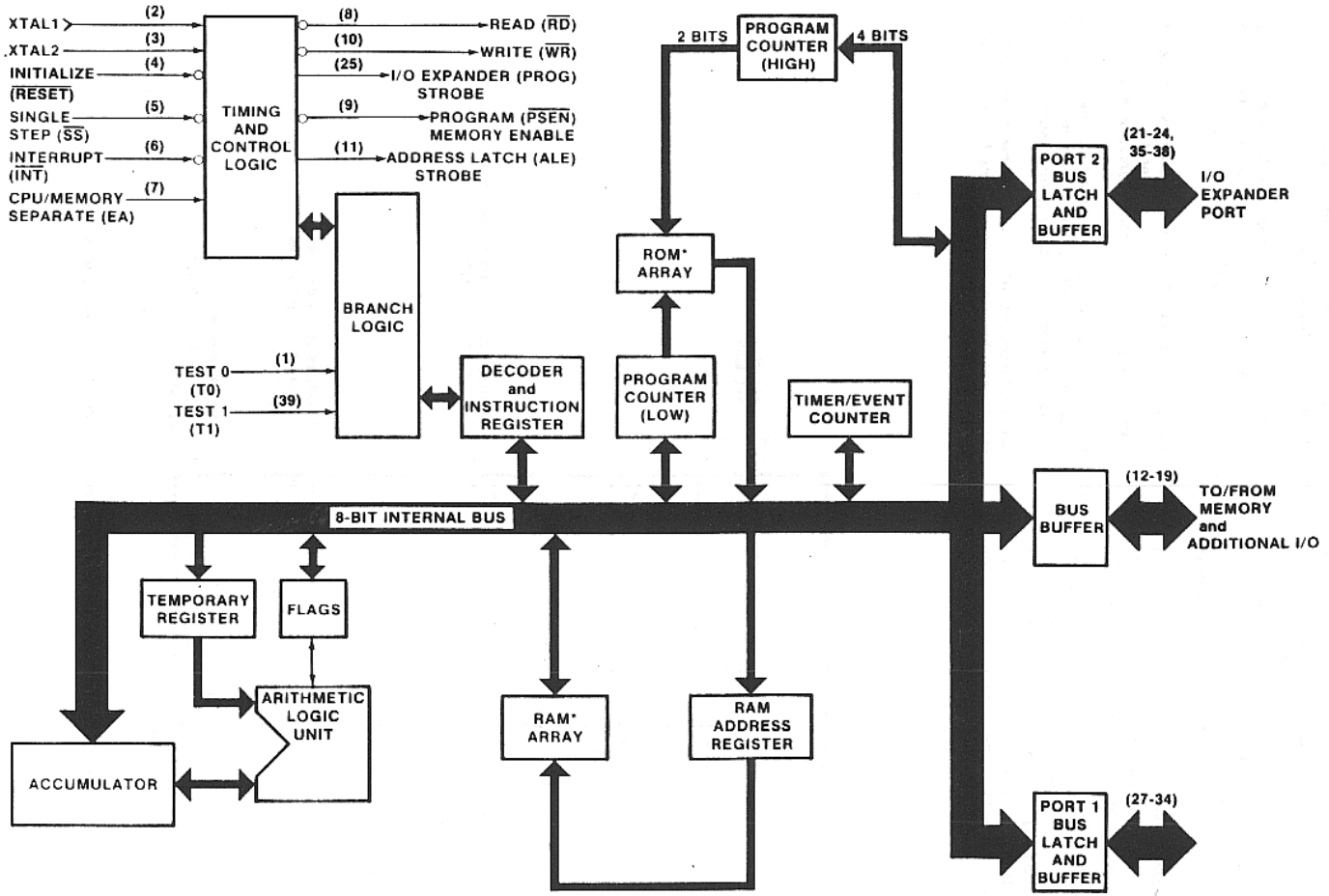
NOTES: The Reset input has a pullup resistor which may be disconnected by a mask program to provide greater flexibility for a Power Reset. (See option 26.)

The INT input does not have a pullup resistor, but a mask programmable resistor can be provided to increase chip flexibility (See option 27.)

The Port 2 pins may be mask programmed to provide transistor drive or open drain capabilities (see options 10-25). (Refer to paragraph on Transparent Improvements.)

Functional Description

The following paragraphs contain the functional description of the major elements of the 48-Series microcomputer/microprocessor. *Figure 1* is a block diagram of the 48-Series devices. The data paths are illustrated in simplified form to show how the various logic elements communicate with each other to implement the instruction set common to all devices.



*ROM AND RAM CAPACITIES

INS8048 - 1K x 8 ROM - 64 x 8 RAM
INS8049 - 2K x 8 ROM - 128 x 8 RAM
INS8050 - 4K x 8 ROM - 256 x 8 RAM

POWER SUPPLY

V_{CC} -(40) +5 POWER SUPPLY
V_{DD} -(26) STANDBY SUPPLY
V_{SS} -(20) GND

NOTE: Applicable pinout numbers are included within parentheses

FIGURE 1. 48-Series Block Diagram

Program Memory

The Program Memory (ROM) contained on the INS8048/49/50 devices is comprised of 1024, 2048 or 4096 8-bit bytes, respectively. As is seen by examining the 48-Series instruction set, these bytes may be program instructions, program data or ROM addressing data. The ROM for the above devices must be mask programmed at the National Semiconductor factory. The ROMless microprocessors, INS8035, INS8039 and INS8040 use external program memory. This makes program development straightforward using standard UV erasable PROMs to emulate a possible future single chip (using the on-board ROM) system. ROM addressing, up to a maximum of 4K, is accomplished by a 12-bit Program Counter (PC). The INS8048 and INS8049 will automatically address external memory when the boundary of their internal memories. 1K and 2K respectively, are exceeded. The binary value of the address selects one of the 8-bit bytes contained in ROM. A new address is loaded into the PC register during each instruction cycle. Unless the instruction is a transfer of control instruction, the PC register is loaded with the next sequential binary count value.

With reference to the Program Memory Map (see *Figure 2*) there are three ROM addresses which provide for the control of the microcomputers.

1. Memory Location 0000-Resetting the Reset (negative true) input to the microcomputer forces the first instruction to be fetched from address 0000.

2. Memory Location 0003 - Asserting the Interrupt (negative true) input to the microcomputer (when interrupt is enabled) forces a jump to subroutine.

3. Memory Location 0007 - A timer/counter interrupt that results from timer/counter overflow (when enabled) forcing a jump to subroutine.

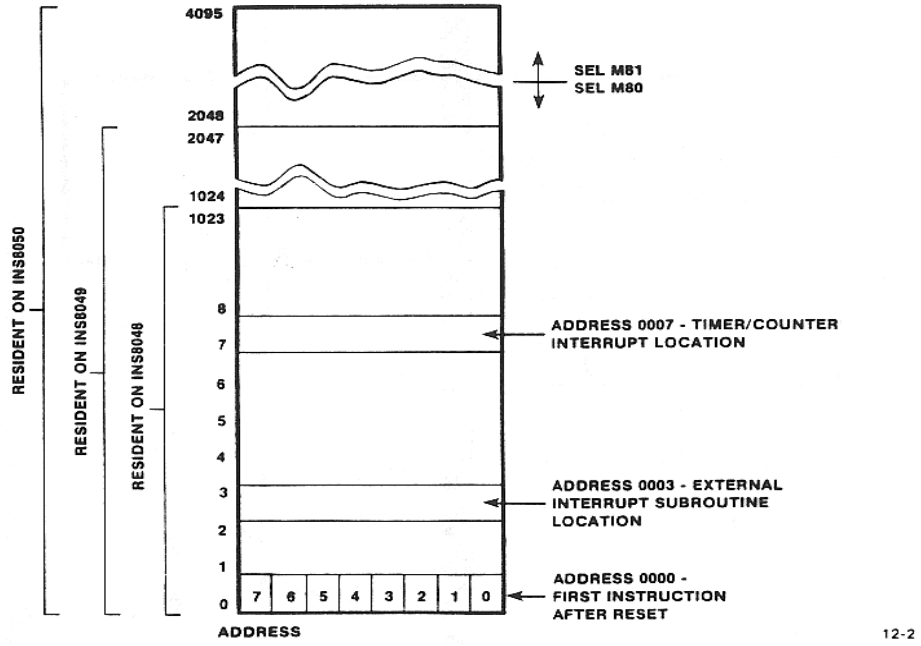


FIGURE 2. INS8048/49/50 Resident ROM Program Memory Map

Data Memory (RAM)

The resident RAM data memory is arranged as 64 (INS8035/8048), 128 (INS8039/8049) or 256 (INS8040/8050) bytes. RAM addressing is implemented indirectly via either of two 8-bit RAM pointer registers RO and R1. These pointer registers are essentially the first two locations in the RAM (see *Figure 3*), addresses 000 and 001. RAM addressing may also be performed directly by 11 direct register instructions. The pointer register area of the RAM array is made up of eight working registers that occupy either the first bank (0). locations (0 to 7), or the second bank (1), locations 24-31. The second bank of working registers is selected by using the Register Bank Switch instruction (SEL RB). If this bank is not used for working registers, it can be used as user RAM.

There is an 8-level stack after Bank 0 that occupies address locations 8 to 23. These RAM locations are addressed indirectly through R0, R1 or the 3-bit Stack Pointer (SP). The stack pointer keeps track of the return address and pushes each return address down into the stack. There are 8 levels of subroutine nesting possible in the stack because each address occupies 10 bits or more using two bytes in RAM. When the level of subroutine nesting is less than 8, the stacks not used may be utilized as user RAM locations.

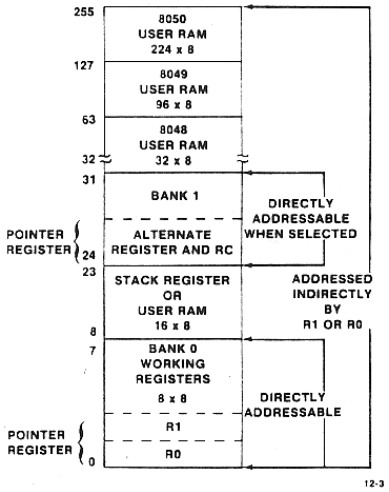


FIGURE 3. 48-Series Resident RAM Data Memory Map

Input/Output

The 48-Series devices have 27 lines of input/output organized as three, 8-bit ports plus three test inputs. The three ports may be used as inputs, outputs or bidirectional ports. Ports 1 and 2 differ from port 3 (Bus Port) in that they are quasi-bidirectional ports. Ports 1 and 2 can be used as input and output while being statically latched. If more I/O lines are required. Port 1 and/or Port 2 can also serve as a 4-bit I/O bus expander when used in conjunction with the INS8243 I/O Expander.

National has designed two options for the port current, drive in addition to the standard TTL drive of 100 µA at 2.4 volts (see *Figure 4*) as follows:

A. **Transistor Drive** - An enhancement mode device to ground and V_{cc}. If the port pin is at 1.5V, the minimum current supplied from V_{cc} is 1.5mA for the output. This output satisfies the typical current for driving a transistor. This output may be turned off under program control.

B. **Open Drain** - When a logic 1 is written, the output will supply less than 10 µA. When a logic 0 is written, the output will supply at least 2mA at 0.4V to ground.

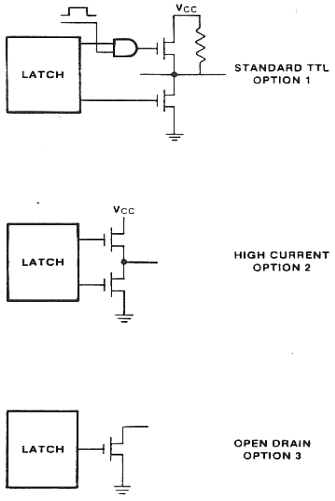


FIGURE 4. Input/Output Options

The bus port is a true bidirectional port and is either statically latched or synchronous. It can be written to using WR strobe or read from using RD strobe. During an external program memory fetch, the 8 lower order program counter bits are preset at this port. The addressed instruction appears on this bus when PSEN is low. During an external RAM data store instruction, this port presents address and data under control of ALE, RD, and WR.

Transparent Improvements

National has made some additional improvements to the standard industry parts. These include a battery charging circuit, programmable RAM on standby, interrupt pin with hystersis, and programmable current drive. Also these improvements are transparent to the user and as noted, some options are programmed at the factory.

Programmable RAM on Standby during POWER down MODE

Battery backed applications are accomplished by programming the minimum amount of RAM kept alive during standby. At 32 words, the National 48-Series consumes only 3 mA at a minimum 2.2 volts. (See DC Electrical Parameters). The banks of RAM are individually mask programmable in groups of 32 words.

During the power down mode, V%lDD%l which normally maintains the RAM cells is the only pin which receives power V%lCC%l which serves the CPU and ports is dropped from normal 5 volts to 0 volt, while the CPU is reset so that the RAM cells are unaltered by the loss of power. When power is restored the processor goes through the normal power-on procedure.

Battery Charging Circuit

All 48-Series devices contain a circuit to provide external battery charging capabilities. Power for all on-board circuits are provided by V%lCC%l (pin-40). As shown in *Figure 5* under normal operating conditions the RESET input is a logic high holding the internal switch in the closed position. V%lCC%l is supplied to the program selectable portion of the RAM array through the closed contact of the internal switch. The normally closed contacts of the switch also provide charging power to the external NiCad cells. In the event of power failure, the RESET pin must be pulled low before V%lCC%l drops below 4.5 volts in order to guarantee the RAM will not loose data. When the RESET pin becomes a logic low (OV) the internal switch is forced to the open condition. DC power to sustain the desired RAM data is provided by the two NiCad batteries (approximately 2.2 volts). Normally, approximately 5 volts are required to provide RAM data protection in the event of a power failure. National's innovative advances in NMOS technology provide the user with a RAM that requires 50% less voltage and 10% of the power to protect data during power failure. The on-chip charging circuit and lower RAM power requirements provide the user with a twofold saving; no external circuits required for the battery charging and only 2 NiCad cells as opposed to the normal requirement of 4 to 5 NiCad cells.

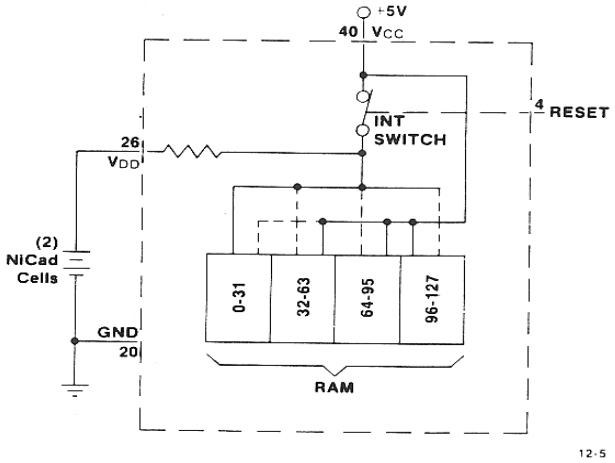


FIGURE 5. Battery Charging Circuit

Counter Increment, Nonincrement Option (Option 28)

National Semiconductor has designed the 48-Series to conform with either of the two versions presently available. The user may select the device suitable for his application. The difference in the devices is as follows:

1. One or more pulses applied to the input of the stopped counter causes the counter to increment by one when restarted.
2. The aforementioned incrementing of the stopped counter by input pulses is eliminated when the counter is restarted.

National Semiconductor accomplishes either option by mask programming at the factory.

Instruction Set

Table 1 details the 95 instructions common to both the microcomputers and the microprocessors. The table provides the mnemonic, function and description, instruction code, number of cycles and, where applicable, flag settings.

Table 1 Instruction Set

					FLAGS			
MNEMONIC	**FUNCTION**	**DESCRIPTION**	**CYCLES**	**BYTES**	C	AC	F0	F1
		CONTROL						
ENI		Enable the External Interrupt input.	1	1				
DISI		Disable the External Interrupt input.	1	1				
ENTO CLK		Enable TO as the Clock Output.	1	1				
SEL MB0	(DBF)<--0	Select Bank 0 (locations 0 - 2047) of Program Memory.	1	1				
SEL MB1	(DBF)<--1	Select Bank 1 (locations 2048 - 4095) of Program Memory.	1	1				
SEL RB0	(BS)<--0	Select Bank 0 (locations 0 - 7) of Data Memory	1	1				
SEL RB1	(BS)<--1	Select Bank 1 (locations 24 - 31) of Data Memory.	1	1				
		DATA MOVES						
MOV A. data	(A)<--data	Move Immediate the specified data into the Accumulator.	2	2				
MOVE A. Rr	(A)<--(Rr); r = 0 - 7	Move the contents of the designated registers into the Accumulator.	1	1				
MOV A, @ Rr	(A)<--((Rr));r = 0 - 1	Move Indirect the contents of data memory location into the Accumulator.	1	1				
MOV A, PSW	(A)<--(PSW)	Move contents of the Program Status Word into the Accumulator.	1	1				
MOV Rr. data	(Rr)<--data; r = 0 - 7	Move Immediate the specified data into the designated register.	2	2				
MOV Rr. A	(Rr)<--(A);r = 0 - 7	Move Accumulator contents into the designated register.	1	1				
MOV @ Rr. A	((Rr))<--(A);r = 0 - 1	Move indirect Accumulator contents into data memory location.	1	1				
MOV @ Rr. Data	((Rr))<--data;r = 0 - 1	Move Immediate the specified data into data memory.	2	2				
MOV PSW. A	(PSW)<--(A)	Move contents of Accumulator into the Program Status Word.	1	1				
MOVP A. @ A	(PC 0 - 7)<--(A) (A)<--((PC))	Move the content of program memory location in the current page addressed by the content of accumulator into the accumulator.	2	1				
MOVP3 A. @ A	(PC 0 - 7)<--(A) (PC 8-10)<--011 (A)<--((PCC))	Move the content of program memory location in page 3 address by the content of accumulator into the accumulator.	2	1				
MOVX A. @ R	(A)<--((Rr));r = 0 - 1	Move Indirect the contents of external data memory into the Accumulator.	2	1				
MOVX @ R.A	((Rr))<--(A);r = 0 - 1	Move Indirect the contents of the Accumulator into external data memory.	2	1				
XCH A. Rr	(A)<--<--(Rr);r = 0 - 7	Exchange the Accumulator and designated register's contents.	1	1				

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS			
					C	AC	F0	F1
		DATA MOVES						
XCH A, @ Rr	(A)-><-((Rr)); r = 0 - 1	Exchange Indirect contents of Accumulator and location in data memory.	1	1				
XCHD A, @ Rr	(A 0-3)--><--(((Rr))0 -3); r = 0 – 1	Exchange Indirect 4-bit contents of Accumulator and data memory.	1	1				
EN TCNTI		Enable Internal Interrupt Flag for Timer/Counter output.	1	1				
DIS TCNTI		Disable Internal Interrupt Flag for Timer/Counter output.	1	1				
MOV A, T	(A)<--(T)	Move contents of Timer/Counter into Accumulator.	1	1				
MOV T, A	(T)<--(A)	Move contents of Accumulator into Timer/Counter.	1	1				
STOP TCNT		Stop Count for Event Counter.	1	1				
STRT CNT		Start Count for Event Counter.	1	1				
STRT T		Start Count for Timer.	1	1				
		ACCUMULATOR						
ADD A, data	(A)<--(A) + data	Add Immediate the specified Data to the Accumulator.	2	2	·			
ADD A, Rr	(A)<--(A) + (Rr) for r = 0 – 7	Add contents of designated register to the Accumulator.	1	1	·	·		
ADD A, @ Rr	(A)<--(A) + ((Rr)) for r = 0 – 1	Add Indirect the contents the data memory location to the Accumulator.	1	1	·	·		
ADDC A, data	(A)<--(A) (C) – data	Add Immediate with carry the specified data to the Accumulator.	2		·	·		
ADDC A, Rr	(A)<--(A) + (C) + (Rr) for r = 0 – 7	Add with carry the contents of the designated register to the Accumulator.	1	1	·	·		
ADDC A, @ Rr	(A)<--(A) + (C) + (Rr) for r = 0 – 1	Add indirect with carry the contents of data memory location to the Accumulator.	1	1	·	·		
ANLA A, data	(A)<--(A) AND data	Logical AND specified Immediate Data with Accumulator.	2	2		·		
ANL A, Rr	(A)<--(A) AND (Rr) for r = 0 – 7	Logical AND contents of designated register with Accumulator.	1	1				
ANL A, @ Rr	(A)<--(A) AND ((Rr)) for r = 0 – 1	Logical AND Indirect the contents of data memory with Accumulator.	1	1				
CPL A	(A)<--NOT (A)	Complement the contents of the Accumulator.	1	1				
CLR A	(A)<--0	CLEAR the contents of the Accumulator.	1	1				
DA A		DECIMAL ADJUST the contents of the Accumulator.	1	1	·			
DEC A	(A)<--(A) - 1	DECREMENT by 1 the accumulator's contents.	1	1				
INC A	(A)<--(A) + 1	Increment by 1 the accumulator's contents.	1	1				
ORL A data	(A)<--(A) OR data	Logical OR specified immediate data with Accumulator.	2	2				
ORL A, Rr	(A)<--(A) OR (Rr) for r = 0 – 7	Logical OR contents of designated register with Accumulator.	1	1				
ORL A, @ Rr	(A)<--(A) OR ((Rr)) for r = 0 – 1	Logical OR Indirect the contents of data memory location with Accumulator.	1	1				
RLA	(An + 1)<--(An) (A_0)<--(A_7) for n = 0 – 6	Rotate Accumulator left by 1-bit without carry.	1	1				
RLC A	(An+1)<--(An); n=0-6 (A_0)<--(C) (C)<--(A_7)	Rotate Accumulator left by 1-bit through carry.	1	1	·			
RR A	(An)<--(An+1); n=0-6 (A_7)<--(A_0)	Rotate Accumulator right by 1-bit without carry.	1	1				

MNEMONIC	FUNCTION	DESCRIPTION	CYCLES	BYTES	FLAGS			
					C	AC	F0	F1
		ACCUMULATOR						
RRO A	(An) (An+1); n+0-6	Rotate Accumulator right by 1-bit through carry.	1	1	*			
	(A_7)<--(C)							
SWAP A	(A_{4-7})<--(A_{0-3})	Swap the 24-bit nibbles in the Accumulator.	1	1				
XRL A. data	(A)<--(A) XOR data	Logical XOR specified immediate data with Accumulator.	2	2				
XRL A. Rr	(A)<--(A) XOR (Rr) for r = 0 – 7	Logical XOR contents of designated register with Accumulator.	1	1				
XRL A. @ Rr	(A)<--(A) XOR ((Rr)) for r = 0 – 1	Logical XOR Indirect the contents of data memory location with Accumulator.	1	1				
		BRANCH						
DJNZ Rr. addr	(Rr)<--(Rr) - 1; r = 0-7 if (Rr) = 0;	Decrement the specified register and test contents.	2	2				
	(PC 0-7)<--addr							
JBb addr	(PC 0-7)<--addr if Bb=1	Jump to specified address if Accumulator bit is set.	2	2				
	(PC)<--(PC) + 2 if Bb=0							
JC addr	(PC 0-7)<--addr if C=1	Jump to specified address if carry flag is set	2	2				
	(PC)<--(PC) +2 if C=0							
JF0 addr	(PC 0-7)<--addr if F0=1	Jump to specified address if Flag F0 is set.	2	2				
	(PC)<--(PC) + 2 if F0=0							
JFI addr	(PC 0-7)<--addr if F1=1	Jump to specified address if Flag F1 is set.	2	2				
	(PC)<--(PC) + 2 if F1=0							
JMP addr	(PC 8-10)<--addr 8-10	Direct Jump to specified address within the 2K address block.	2	2				
	(PC 0-7)<--addr 0-7							
	(PC 11)<--DBF							
JMPP @ A	(PC 0-7)<--((A))	Jump indirect to specified address pointed to by the accumuiator in current page.	2	1				
JNC addr	(PC 0-7)<--addr if C=0	Jump to specified address if carry flag is low.	2	2				
	(PC)<--(PC) + 2 if C=1							
JNI addr	(PC 0-7)<--addr if 1=0	Jump to specified address if interrupt is low.	2	2				
	(PC)<--(PC) + 2 if 1=1							
JNT0 addr	(PC 0-7)<--addr if T0=0	Jump to specified address if Test 0 is low.	2	2				
	(PC)<--(PC) + 2 if TO=1							
JNT1 addr	(PC 0-7)<--addr if T1=0	Jump to specified address if Test 1 is low.	2	2				
	(PC)<--(PC) + 2 if T1=1							
JNZ addr	(PC 0-7)<--addr if A??0	Jump to specified address if accumulator is non-zero.	2	2				
	(PC)<--(PC) + 2 if A=0							
JTF addr	(PC 0-7)<--addr if TF=1	Jump to specified address if Timer Flag is set to 1.	2	2				
	(PC)<--(PC) + 2 if TF=0							
JT0 addr	(PC 0-7)<--addr if T0=1	Jump to specified address if Test 0 is a 1.	2	2				
	(PC)<--(PC) + 2 if T0=0							
JT1 addr	(PC 0-7)<--addr if T1=1	Jump to specified address if Test 1 is a 1.	2	2				
	(PC)<--(PC) + 2 if T1=0							
JZ addr	(PC 0-7)<--addr if A=0	Jump to specified address if Accumulator is 0.	2	2				
	(PC)<--(PC) + 2 if A=0							

					FLAGS			
MNEMONIC	**FUNCTION**	**DESCRIPTION**	**CYCLES**	**BYTES**	C	A C	F0	F1
		INPUT/OUTPUT						
ANL BUS, data	(BUS)<--(BUS) AND data	Logical AND Immediate specified data with contents of BUS.	2	2				
ANL P_p. data	(P_p)<--(P_p) AND data; p = 1-2	Logical AND immediate specified data with designated port (1 or 2).	2	2				
ANLD P_p A	(P_p)<--(P_p) AND (A 0-3); p = 4-7	Logical AND contents of Accumulator with designated port (4-7).	2	1				
INS A. BUS	(A)<--(BUS)	Input strobed BUS data into Accumulator	2	1				
MOVD A. P_p	(A 0-3)<--(P_p); p = 4-7 (A 4-7)<--0	Move contents of designated port (4-7) into Accumulator.	2	1				
MOVD P_p. A	(P_p)<--(A 0-3); p = 4-7	Move contents of Accumulator to designated port (4-7).	1	1				
ORL BUS, data	(BUS)<--(BUS) OR data	Logical OR Immediate specified data with contents of BUS.	2	2				
ORLD P_p. A	(P_p)<--(P_p) OR (A 0-3); p = 4-7	Logical OR contents of Accumulator with designated port (4-7).	1	1				
ORL P_p data	(P_p)<--(P_p) OR data; p = 1-2.	Logical OR Immediate specified data with designated port (1-2).	2	2				
OUTL BUS. A	(BUS)<--(A)	Output contents of Accumulator onto BUS.	1	1				
OUTL P_p. A	(P_p)<--(A); p = 1-2	Output contents of Accumulator to designated port (1-2).	1	1				
		REGISTERS						
DEC Rr	(Rr)<--(Rr)-1; r = 0-7	Decrement by 1 contents of designated register.	1	1				
INC Rr	(Rr)<--(Rr)-1; r = 0-7	Increment by 1 contents of designated register.	1	1				
INC @ Rr	((Rr))<--((Rr))+1; r = 0-1.	Increment Indirect by 1 the contents of data memory location.	1	1				
		SUBROUTINE						
CALL addr	((SP))<--(PC)	Call designated Subroutine.	2	2				
	((SP))<--(PSW 4-7)							
	(SP)<--(SP)+1							
	(PC8-10)<--addr 8-10							
	(PC 0-7)<--addr 0-7							
	(PC 11)<--DBF							
RET	(SP)<--(SP)-1	Return from Subroutine without restoring Program Status Word.	2	1				
	(PC)<--((SP))							
RETR	(SP)<--(SP)-1	Return from Subroutine restoring Program Status Word.	2	1	·			
	(PC)<--((SP))							
	(PSW 4-7)<--((SP))							
		FLAGS						
CPL C	(C)<--NOT (C)	Complement Content of carry bit.	1	1	·			
CPL F0	(F0)<--NOT (F0)	Complement Content of Flag F0.	1	1			·	
CPL F1	(F1)<--NOT (F1)	Complement Content of Flag F1.	1	1				·
CLR C	(C)<--0	Clear content of carry bit to 0.	1	1	·			
CLR F0	(F0)<--0	Clear content of Flag 0 to 0.	1	1			·	
CLR F1	(F1)<--0	Clear content of Flag 1 to 0.	1	1				·

Symbol Definitions

SYMBOL	DESCRIPTION
A	The Accumulator
AC	The Auxiliary Carry Flag
addr	Program Memory Address (12 bits)
Bb	Bit Designator (b = 0 - 7)
BS	The Bank Switch
BUS	The BUS Port
C	Carry Flag
CLK	Clock Signal
CNT	Event Counter
D	Nibble Designator (4 bits)
data	Number or Expression (8 bits)
DBF	Memory Bank Flip-Flop
F_0 F_1	Flags 0.1
I	Interrupt
P	"In-Page" Operation Designator

SYMBOL	DESCRIPTION
P_p	Port Designator (p = 1. 2 or 4 - 7)
PSW	Program Status Word
Rr	Register Designator (r = 0, 1 or 0 - 7)
SP	Stack Pointer
T	Timer
TF	Timer Flag
T_0 T_1	Testable Flags 0. 1
X	External RAM
#	Prefix for Immediate Data
@	Prefix for Indirect Address
$	Program Counter's Current Value
(x)	Contents of External RAM Location
((xx))	Contents of Memory Location Addressed by the Contents of External RAM Location.
←	Replaced By

TYPICAL APPLICATIONS

Figure 6 shows a typical way to use the 48-Series Microcomputers in a stand-alone system.

- Crystal used is:
  - Series resonant
  - AT cut
  - 1 to 6 MHz or 4 to 11 MHZ
- Port 1 and 2 can be programmed for these three options
  - TTL Drive 125 µa @ 2.4V (option 1)
  - Transistor Drive 1.5 mA @ 1.5V (option 2)
  - Open Drain 10 µA Maximum at 0.40 volt (option 3)
- Bus Port is standard TTL compatible

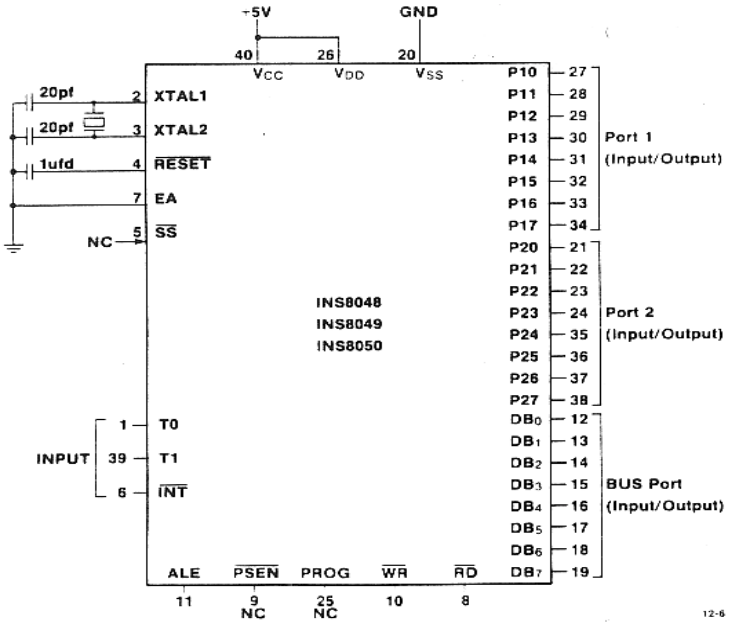


FIGURE 6. Stand-alone INS8048/49/50

TYPICAL APPLICATIONS (Cont'd)

Figure 7 shows a typical remote data acquisition system with an INS8250 Programmable Asynchronous Communication System which can receive commands or update information from a supervisory computer. The figure also shows an INS8294 CMOS DVM. that receives data at VIN and displays the data on the 7-segment local display unit. Data are transferred from the INS8294 to the INS8049 via National's MICROBUS"

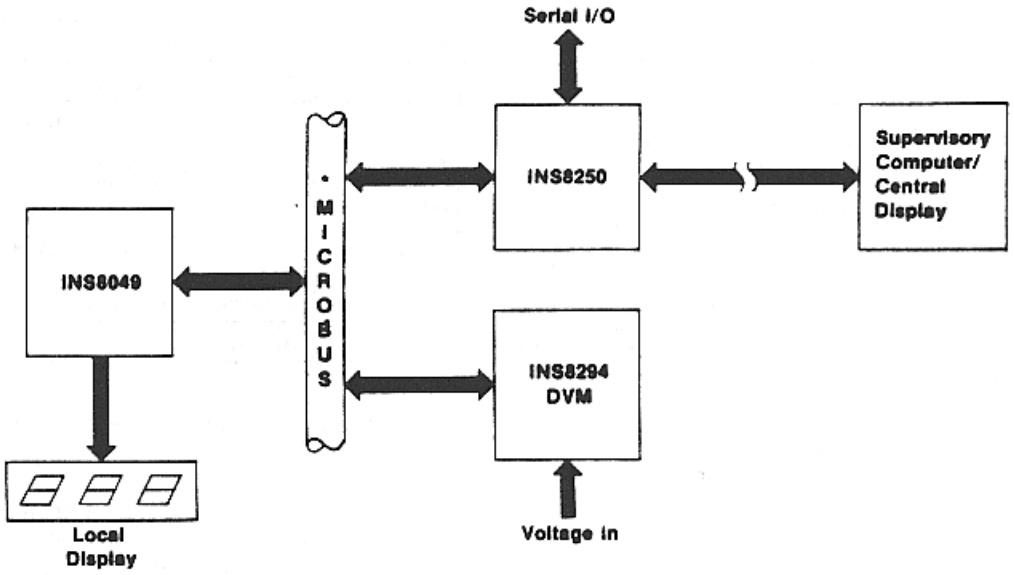
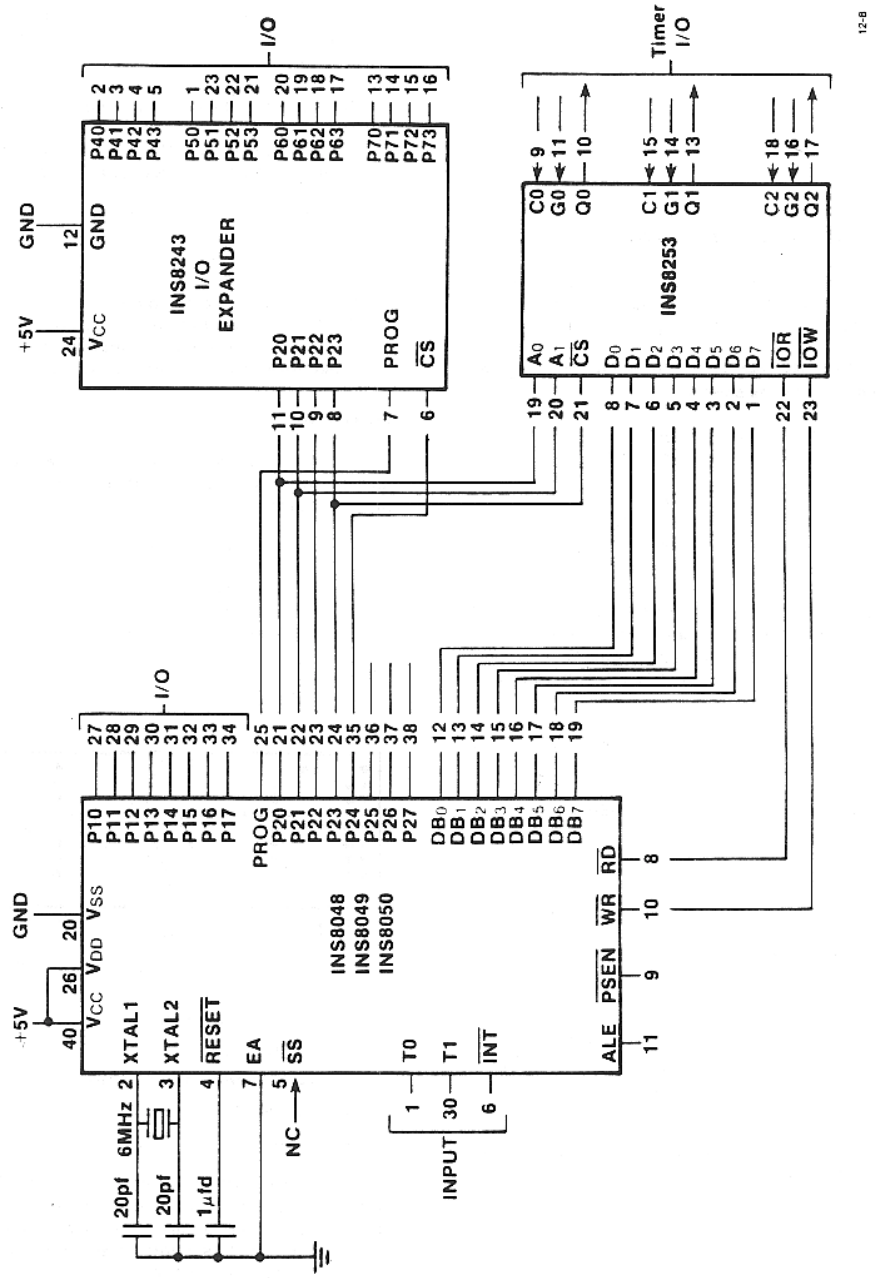


FIGURE 7. Data Acquisition System 12-7

TYPICAL APPLICATIONS (Cont'd)

Figure 8 shows a typical way to add a Input/Output Expander and Programmable Interval Timer to the 48-Series Microprocessors.



12-8

FIGURE 8. INS8253 Interval Timer

INPUT MEDIUM:

EPROM
PAPER TAPE

EPROM:

2716 Total No. of EPROMS
2708

IMPORTANT - EPROM LABELLING

Only one customer program may be included in a single order. The following method must be used to identify the EPROMs comprising a program.

a) The EPROMs used for storing a custom program are designated as shown:

2716:	BLOCK A	0-2047
	BLOCK B	2048 - 4095
2708:	BLOCK A	0 - 1023
	BLOCK B	1024 - 2047
	BLOCK C	2048 - 3071
	BLOCK D	3072 - 4095

b) All EPROMs must be labelled (stickers, paint, etc) with this block designation plus a customer identification number. For example a 4K custom program contained in two 2716's would be labelled:

Customer I.D.	Customer I.D.
A	B
0-2047	2048-4095

Binary Complement Format

Verification

The customer can use software (the listing) or hardware (EPROMs) to verify the program. He will receive a verification listing and a set of EPROMs programmed and tested with tapes generated by the NSC Mask Programming System (MPS). He will be asked for a GO/NO GO response within a week after receipt of the listing and EPROMs.

VERIFICATION LISTING

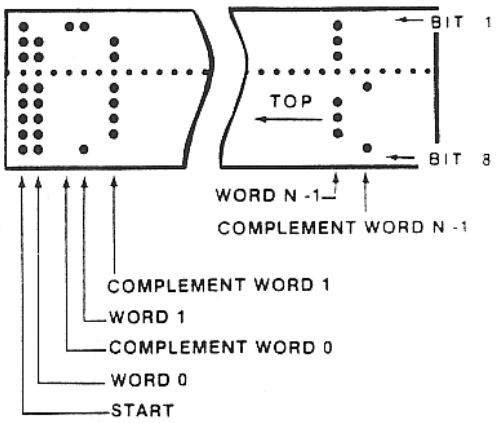
The verification listing has six sections:

1. A cover sheet with provision for "STOP, DO NOT PROCEED" or "VERIFICATION CERTIFIED" signatures.
2. Description of the options he has chosen.
3. A description of the log designations and assumptions used to process the data.
4. A listing of the data submitted by the customer.
5. An error summary.
6. A definition of the standard logic definitions for the ROM and the reduced from of the data. This list shows the output word corresponding to each address coded three ways - binary, octal, and hexadecimal.

Paper Tape

Tapes may only be submitted in binary complement format. The following information should be written on the paper tape.

Company Name
Company I.D. No.
NSC Part No.
A Punch = ("1" or "0")
This is logic (POS or NEG)



Note 1: Tape must be blank except for the data words.
Note 2: Tape must start with a rubout character.
Note 3: Data is comprised of two words, the first being the actual data and the second being the complement of the data.

Ordering Information for Custom Programmed Parts

The following information must be submitted with each customer microcomputer program. An order will not be processed unless it is accompanied by this information. This form acts as a Traveler from Customer through Customer Service to ROM programming. Please retain a copy of this form to compare against the verification listing. The form will be sent back to the customer by Customer Service.

	National Microcomputer Part Number
	ROM Letter Code (National Use Only)
Name	Date
Address	Customer Print or I.D. No.
City State Zip	Purchase Order No.
Telephone ( )	Name of person National can contact (Print)
Authorized Signature	Date

OPTIONS

1. Device Type (Check one)
   8048-6 (6MHz) 8049-6 8050-6
   8048-11(11MHz) 8049-11 8050-11

   A. Input Medium (see attached for approved Formats)

Paper Tape 8748 EPROM 2716
8048 2708
8049 Total No. of EPROMS

   B. Does the ROM pattern make use of the transparent improvements (options)

      YES NO

      If yes; complete the following:

Options 2-9. Banks of RAM on Standby (Check each box applicable to device type. 1 = RAM Bank on Standby, 0 = Not on Standby)

2.0-31	(8048, 8049, 8050)
3.32-63	(8048, 8049, 8050)
4.64-95	(8049, 8050, only)
5.96-127	(8049, 8050 only)
6.128-159	(8050 only)
7.160-191	(8050 only)
8.192-223	(8050 only)
9.224-255	(8050 only)

Options 10-25 Port Drive Current Selections: (Check each box with either 1 = Standard (TTL), 2 = High Current or 3 = Open Drain)

Port 1

Option	Pin	Bit	Selection
10	10	0	
11	11	1	
12	12	2	
13	13	3	
14	14	4	
15	15	5	
16	16	6	
17	17	7	

Port 2

Option	Pin	Bit	Selection
18	21	0	
19	22	1	
20	23	2	
21	24	3	
22	35	4	
23	36	5	
24	37	6	
25	38	7	

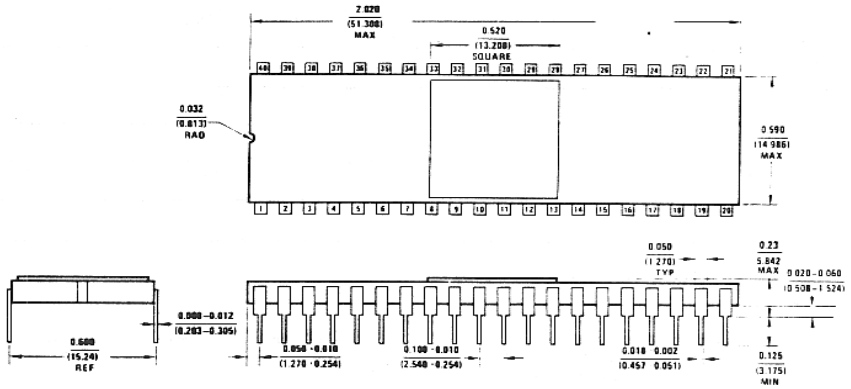
Option 26. Pullup Resistor on Reset Pin (Enter either 0 = NO or 1 = YES (Standard) in Box)

Option 27. Pullup Resistor or Interrupt Pin (Enter 0=NO (Standard) or 1 = YES in Box)

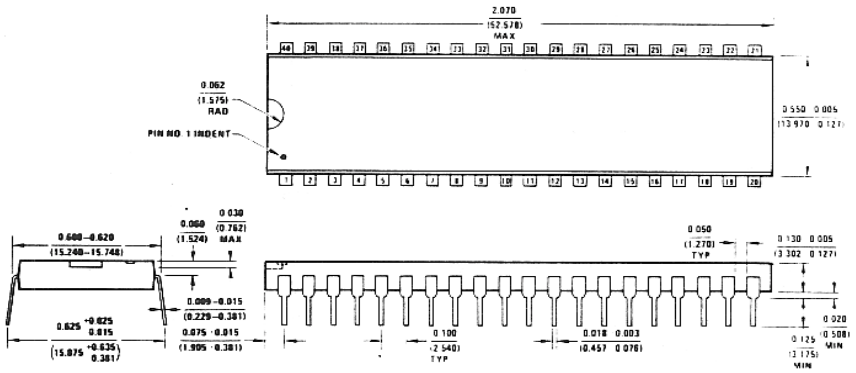
Option 28 Counter Increment. Non-Incremented (enter 0 = Counter Increment (Standard) or 1 = Non-Incremented)

Physical Dimensions

inches (millimeters)



Ceramic Dual-In-Line Package (D)
Order Number INS8048D



Plastic Dual-In-Line Package (N)
Order Number INS8048N

National Semiconductor Corporation
2900 Semiconductor Drive
Santa Clara, California 95051
Tel: (408) 737-5000
TWX: (910) 339-9240

National Semiconductor GmbH
Eisenheimerstrasse 61/11
8000 Munchen 21
West Germany
Tel: (089) 576091
Telex: 05 22772

NS International Inc., Japan
Miyake Building
1-9 Yotsuya, Shinjuku-ku 160
Tokyo, Japan
Tel: (03) 355-3711
TWX: 232 2015 NSCJJ

National Semiconductor (Hong Kong) Ltd.
8th Floor
Cheung Kong Electronic Bldg
4 Hing Yip Street
Kwun Tong
Kowloon, Hong Kong
Tel: 3 899235
Telex: 73866 NSEHK HX
Cable: NATSEMI

NS Electronics Do Brasil
Avda Brigadeiro Faria Lima 844
11 Andar Conjunto 1104
Jardim Paulistano
Sao Paulo, Brasil
Telex:
1121008 CABINE SAO PAULO

NS Electronics Pty Ltd
Cnr. Stud Rd. & Mtn. Highway
Bayswater, Victoria 3153
Australia
Tel: 03 729 6333
Telex: 32096